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November 2013

FCI25N60N

N-Channel SupreMOS[®] MOSFET 600 V, 25 A, 125 m Ω

Features

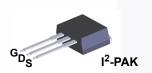
- $R_{DS(on)}$ = 107 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 12.5 A
- Ultra Low Gate Charge (Typ. Q_q = 57 nC)
- Low Effective Output Capacitance (Typ. C_{oss(eff.)} = 262 pF)
- 100% Avalanche Tested
- · RoHS Compliant

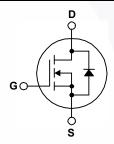
Application

- · Solar Inverter
- AC-DC Power Supply

Description

The SupreMOS® MOSFET is Fairchild Semiconductor's next generation of high voltage super-junction (SJ) technology employing a deep trench filling process that differentiates it from the conventional SJ MOSFETs. This advanced technology and precise process control provides lowest Rsp on-resistance, superior switching performance and ruggedness. SupreMOS MOSFET is suitable for high frequency switching power converter applications such as PFC, server/telecom power, FPD TV power, ATX power, and industrial power applications.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter	FCI25N60N_F102	Unit		
V _{DSS}	Drain to Source Voltage		600	V		
V _{GSS}	Gate to Source Voltage		±30	V		
	Drain Current	- Continuous (T _C = 25°C)	25	^		
I _D	Drain Current	- Continuous (T _C = 100°C)	16	Α		
I _{DM}	Drain Current	- Pulsed (Note 1)	75	Α		
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		861	mJ		
I _{AR}	Avalanche Current (Note 1)		8.3	Α		
E _{AR}	Repetitive Avalanche Energy (Note 1)		2.2	mJ		
dv/dt	MOSFET dv/dt		100	V/ns		
uv/ul	Peak Diode Recovery dv/dt	(Note 3	15	V/IIS		
n	$(T_C = 25^{\circ}C)$		Davis Diaglastics	$(T_C = 25^{\circ}C)$	216	W
P _D Power Dissipation		- Derate Above 25°C	1.72	W/°C		
T _J , T _{STG}	Operating and Storage Temp	erature Range	-55 to +150	°C		
TL	Maximum Lead Temperature	for Soldering, 1/8" from Case for 5 Seconds	300	°C		

Thermal Characteristics

Symbol	Parameter	FCI25N60N_F102	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.58	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	C/VV

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCI25N60N_F102	FCI25N60N	I ² -PAK	Tube	N/A	N/A	50 units

Test Conditions

Min.

Тур.

Max.

Unit

$\label{eq:control} \textbf{Electrical Characteristics} \quad \textbf{T}_{C} = 25^{o} \text{C unless otherwise noted}.$ Parameter

Off Chara	acteristics					
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 1 \text{ mA}, V_{GS} = 0 \text{ V}, T_J = 25^{\circ}\text{C}$	600	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 1 mA, Referenced to 25°C	-	0.74	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 480 V, V _{GS} = 0 V	-	-	10	μА
DSS	Zero Gate Voltage Drain Current	$V_{DS} = 480 \text{ V}, T_{J} = 125^{\circ}\text{C}$	-	-	100	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

Symbol

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	2.0	-	4.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 12.5 A	-	0.107	0.125	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 12.5 A	-		-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz		2520	3352	pF
C _{oss}	Output Capacitance			103	137	pF
C _{rss}	Reverse Transfer Capacitance			3.2	5	pF
C _{oss}	Output Capacitance	V _{DS} = 380 V, V _{GS} = 0 V, f = 1 MHz	- \	55	-	pF
C _{oss(eff.)}	Effective Output Capacitance	$V_{DS} = 0 \text{ V to } 480 \text{ V}, V_{GS} = 0 \text{ V}$	- 1	262	-	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 380 V, I _D = 12.5 A,	-	57	74	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V	-	10	-	nC
Q _{gd}	Gate to Drain "Miller" Charge	(Note 4)	-	18	-	nC
ESR	Equivalent Series Resistance (G-S)	f = 1 MHz	-	1	-	Ω

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	21	52	ns
t _r	Turn-On Rise Time	$V_{DD} = 380 \text{ V}, I_D = 12.5 \text{ A},$	-/	22	54	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 4.7 Ω	-	68	146	ns
t _f	Turn-Off Fall Time	(Note 4)	_	5	20	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current			-	25	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	75	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 12.5 A	-	-	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 12.5 A,	-	370	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	7	//-	μС

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. I_{AS} = 8.3 A, R_{G} = 25 Ω , starting T_{J} = 25°C.
- 3. $I_{SD} \le 25$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le 380$ V, starting T_J = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

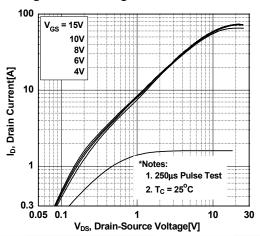


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

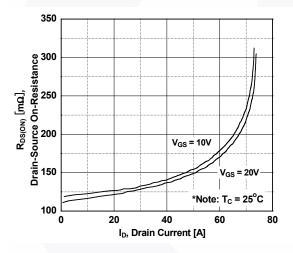


Figure 5. Capacitance Characteristics

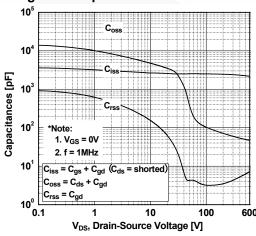


Figure 2. Transfer Characteristics

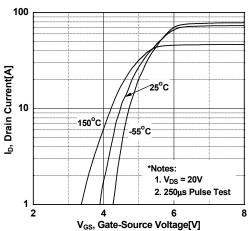


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

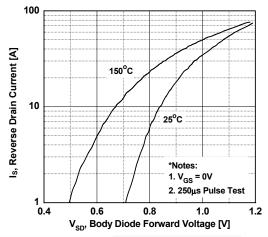
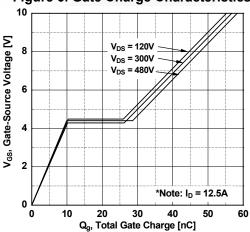
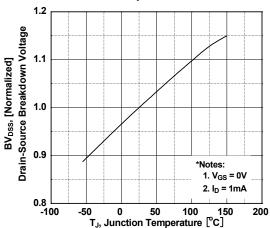


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature



vs. Temperature 3.0

Figure 8. On-Resistance Variation

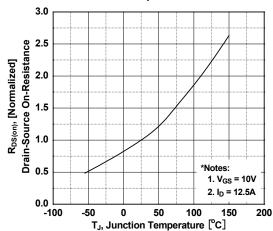


Figure 9. Maximum Safe Operating Area

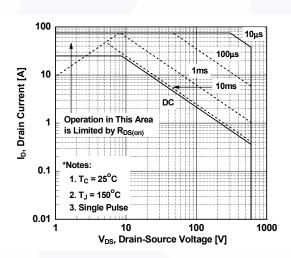


Figure 10. Maximum Drain Current vs. Case Temperature

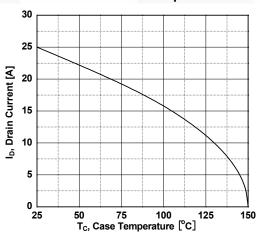
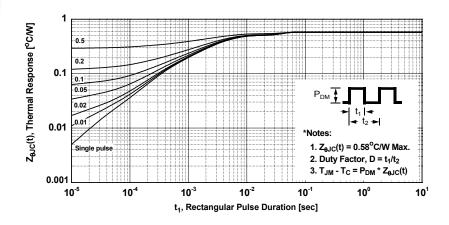


Figure 11. Transient Thermal Response Curve



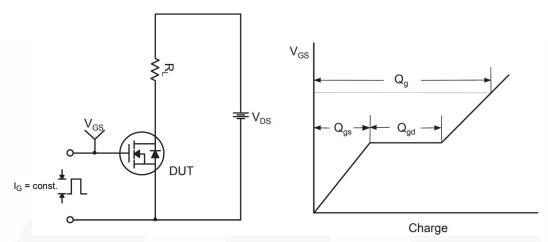


Figure 12. Gate Charge Test Circuit & Waveform

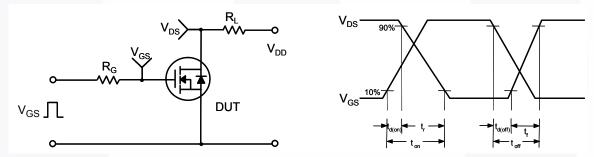


Figure 13. Resistive Switching Test Circuit & Waveforms

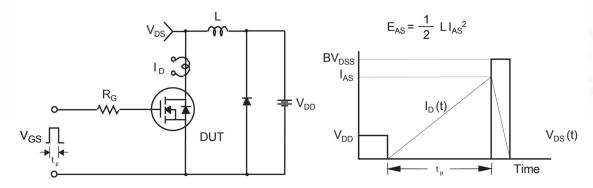


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

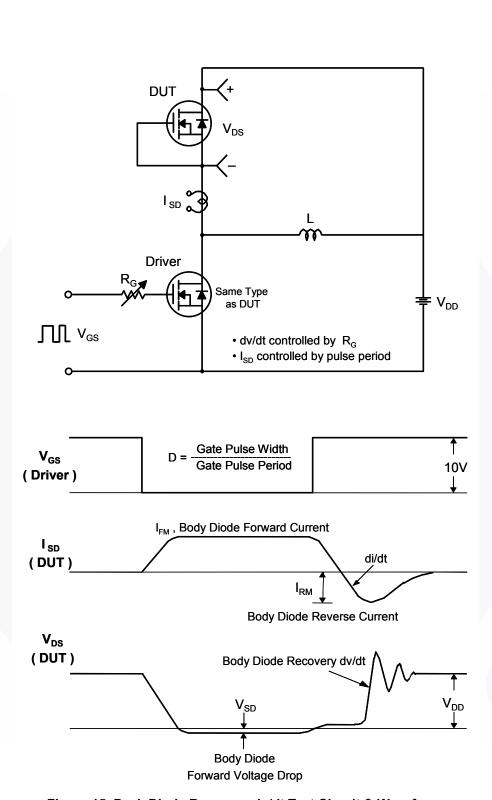


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

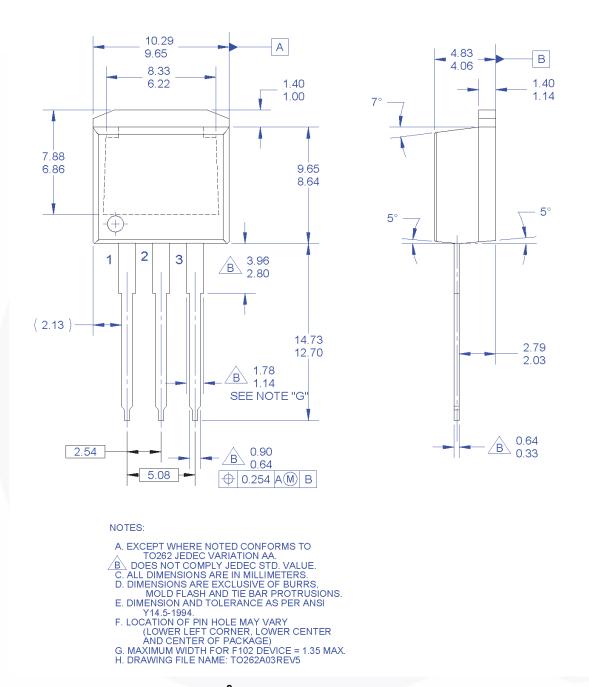


Figure 16. TO262 (I²PAK), Molded, 3-Lead, Jedec Variation AA

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